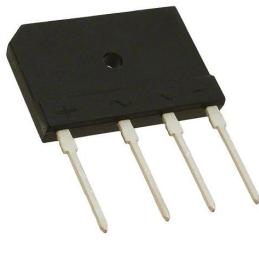


GBJ20005-GBJ2010

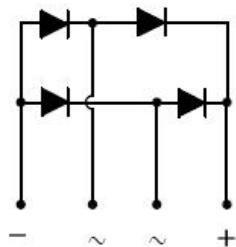
Single-Phase 20.0A Glass Passivated Bridge Rectifier



Features

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: GBJ, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version
- Weight: 6.8 grams(approx)

Maximum Ratings @ $T_A=25^\circ\text{C}$ unless otherwise specified

Type Number	Symbol	GBJ 20005	GBJ 2001	GBJ 2002	GBJ 2004	GBJ 2006	GBJ 2008	GBJ 2010	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_{DC}	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Average rectified output current (with heatsink)@ $T_c = 100^\circ\text{C}$ (without heatsink)@ $T_A = 25^\circ\text{C}$	$I_{F(AV)}$				20	3.5			A
Peak Forward Surge Current,8.3ms single half-sine-wave superimposed on rated load (JEDEC method) @ $T_J = 25^\circ\text{C}$ @ $T_J = 125^\circ\text{C}$	I_{FSM}				320	256			A
I^2t Rating for Fusing ($t < 8.3\text{ms}$)	I^2t				239				A^2s

Electrical Characteristics@ $T_A=25^\circ\text{C}$ unless otherwise specified

Type Number	Symbol	GBJ 20005	GBJ 2001	GBJ 2002	GBJ 2004	GBJ 2006	GBJ 2008	GBJ 2010	Units
Forward Voltage (per element) @ $I_F = 10\text{A}$ @ $I_F = 20\text{A}$	V_F		1.0	1.1					V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$	I_{RM}		5	200					μA
Dielectric Strength	V_{ids}		2500						V
The proposed installation torque Max torque	T_{or}		Typ. 5.0	Max 8.0					Kgf.cm
Typical Junction Capacitance(per leg) (Note 1)	C_J		75						pF

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Type Number	Symbol	GBJ 20005	GBJ 2001	GBJ 2002	GBJ 2004	GBJ 2006	GBJ 2008	GBJ 2010	Units
Typical Thermal Resistance Junction	$R_{\theta JA}$ $R_{\theta JL}$ $R_{\theta JC}$		22	2	1.5				$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J , T_{STC}		-55 to +150						$^\circ\text{C}$

Note: 1- Measured at 1 MHZ and applied reverse voltage of 4.0 VDC.

Ratings and Characteristics Curves

Fig. 1 Forward Current Derating Curve

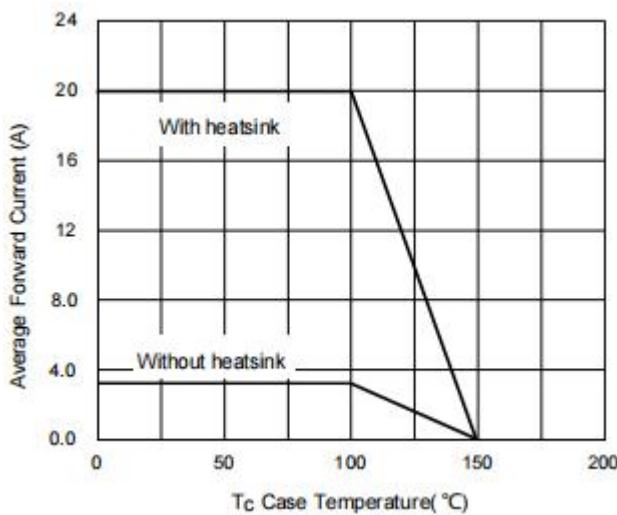


Fig. 2 Typical Forward Characteristics

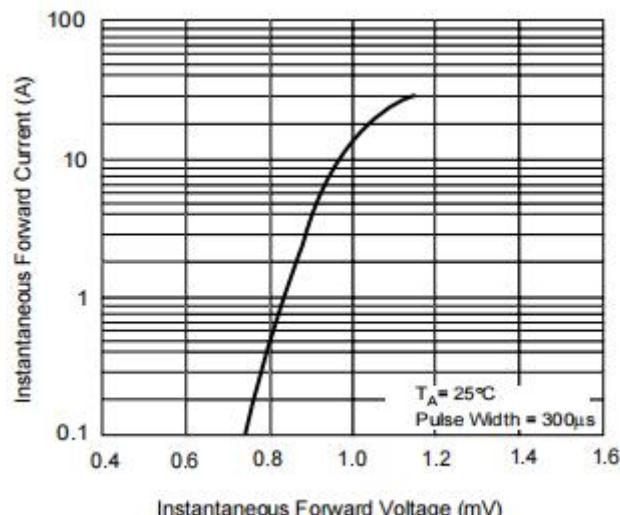


Fig. 3 Forward Surge Current Capability

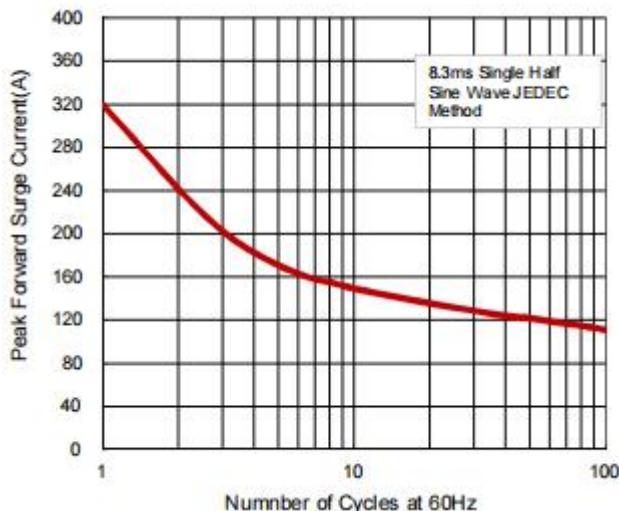
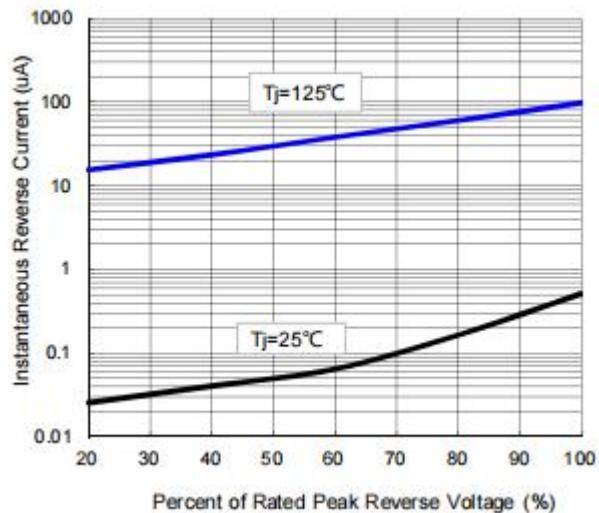


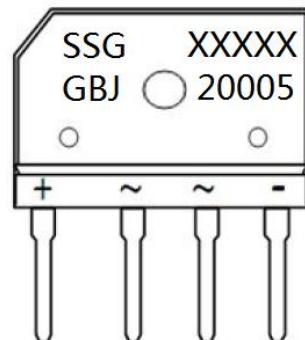
Fig. 4 Typical Reverse Characteristics



Ordering Information

Device	Package	Plating	Shipping
GBJ20005 THRU GBJ2010	GBJ(Pb-Free)	Pure Sn	15pcs / tube

Marking Diagram

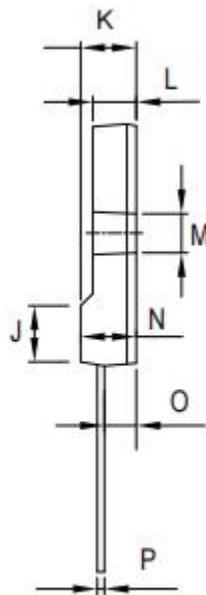
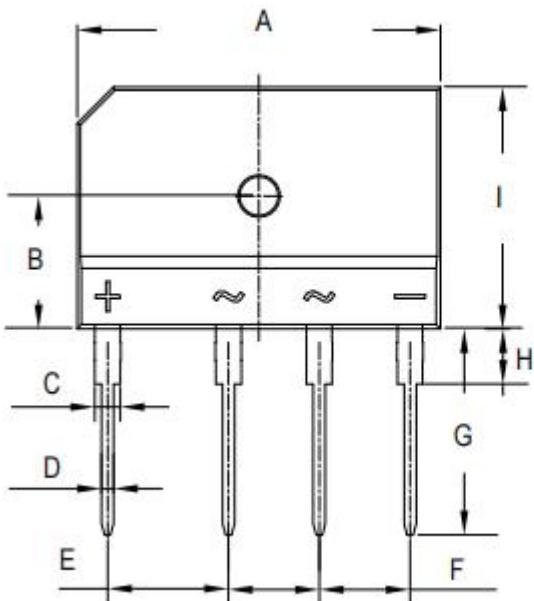


Where XXXXX is YYWWL

SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number
GBJ20005	= Type Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Mechanical Dimensions GBJ (Inches/Millimeters)



Dimensions	Millimeters		Inches	
	Min	Max	Min	Max
A	29.7	30.3	1.169	1.193
B	10.8	11.2	0.425	0.441
C	1.9	2.3	0.075	0.091
D	0.9	1.1	0.035	0.043
E	9.8	10.2	0.386	0.402
F	7.3	7.7	0.287	0.303
G	17.0	18.0	0.699	0.709
H	3.8	4.2	0.150	0.165
I	19.7	20.3	0.776	0.799
J	4.8	5.2	0.189	0.205
K	4.4	4.8	0.173	0.189
L	3.4	3.8	0.134	0.150
M	3.1	3.4	0.122	0.134
N	4.4	4.8	0.173	0.189
O	2.4	2.8	0.094	0.110
P	0.5	0.7	0.020	0.028

Technical Data
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